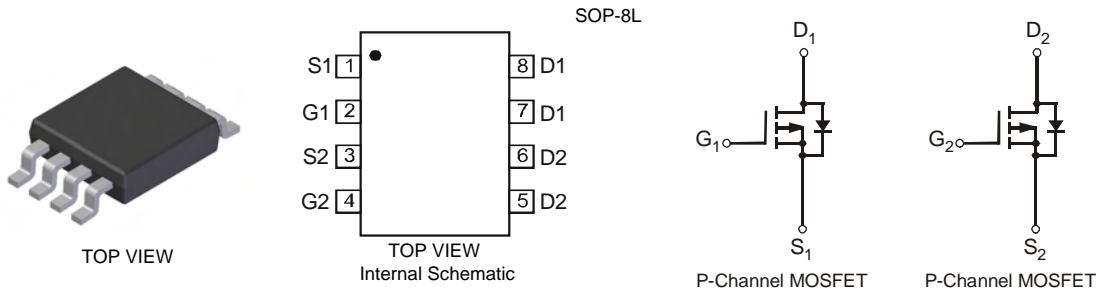


Features

- Dual P-Channel MOSFET
- Low On-Resistance
 - 40mΩ @ $V_{GS} = -4.5V$
 - 70mΩ @ $V_{GS} = -2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Drain Current (Note 1)	Steady State	$T_A = 25^\circ C$	I_D	-5.8	A
		$T_A = 70^\circ C$		-4.6	
Pulsed Drain Current (Note 3)			I_{DM}	-20	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	2.0	W
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	62.5	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on 2 oz., 1" x 1" Copper pads on 2" x 2" FR-4 PCB.
 2. No purposefully added lead.
 3. Pulse width $\leq 10\mu S$, Duty Cycle $\leq 1\%$.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.6	-0.94	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	29 55	40 70	m Ω	$V_{GS} = -4.5V, I_D = -4.6A$ $V_{GS} = -2.5V, I_D = -3.8A$
Forward Transconductance	g_{fs}	—	9	—	S	$V_{DS} = -10V, I_D = -4.6A$
Diode Forward Voltage (Note 5)	V_{SD}	-0.5	-0.72	-1.4	V	$V_{GS} = 0V, I_S = -2.1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	820	—	pF	$V_{DS} = -15V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	200	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	160	—	pF	
Gate Resistance	R_G	—	2.5	—	Ω	$V_{DS} = 0V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	—	10.1	—	nC	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_D = -5.9A$
Gate-Source Charge	Q_{GS}	—	1.5	—		
Gate-Drain Charge	Q_{GD}	—	4.3	—		
Turn-On Delay Time	$t_{d(on)}$	—	4.4	—	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_D = -1A, R_G = 6.0\Omega$
Rise Time	t_r	—	9.9	—		
Turn-Off Delay Time	$t_{d(off)}$	—	28.0	—		
Fall Time	t_f	—	23.4	—		

Notes: 5. Short duration pulse test used to minimize self-heating effect.

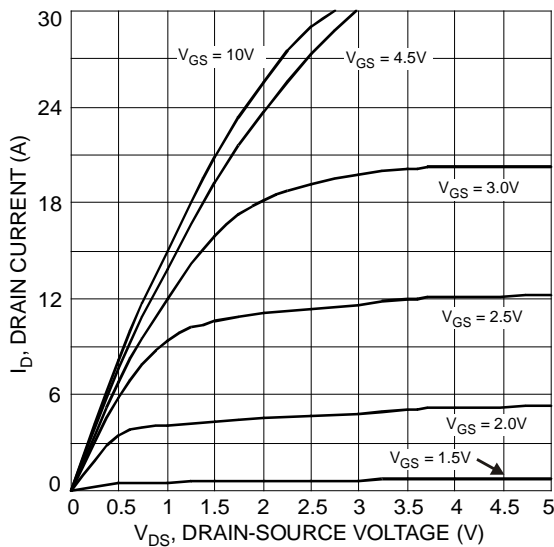


Fig. 1 Typical Output Characteristic

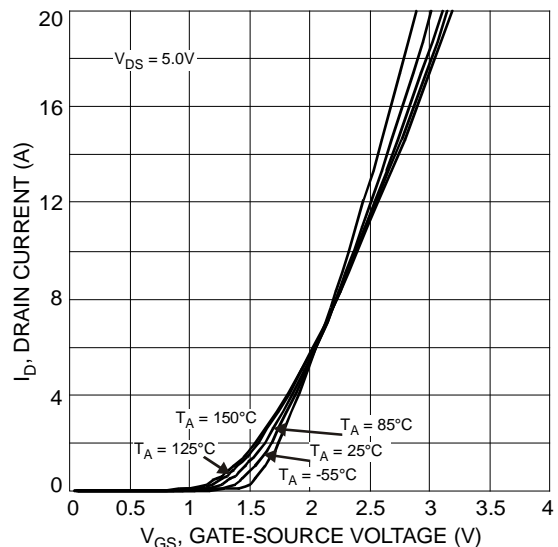


Fig. 2 Typical Transfer Characteristic

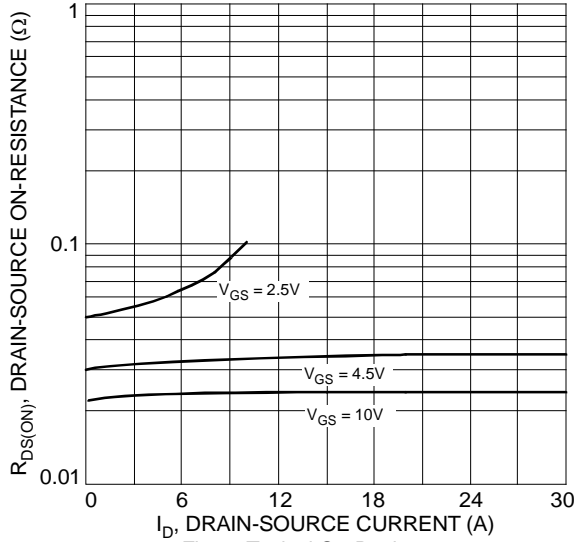


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

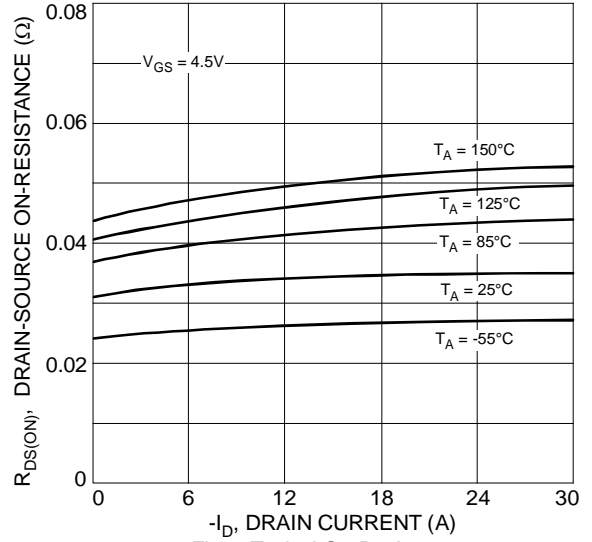


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

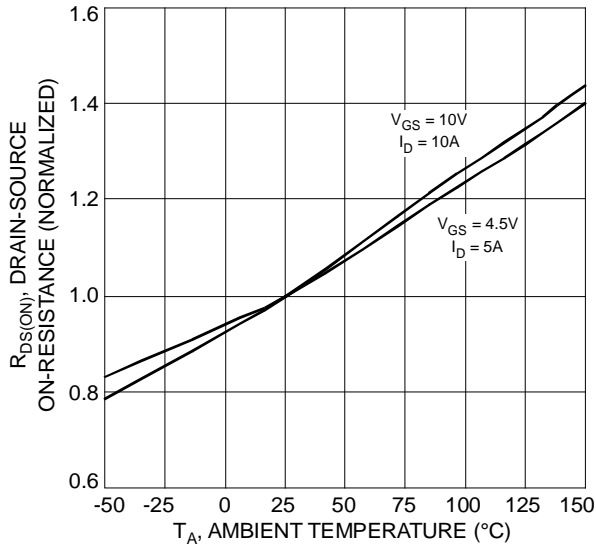


Fig. 5 Normalized On-Resistance vs. Ambient Temperature

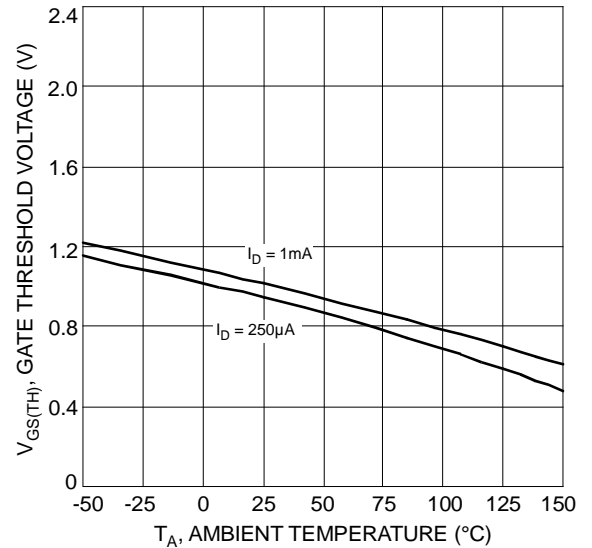


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

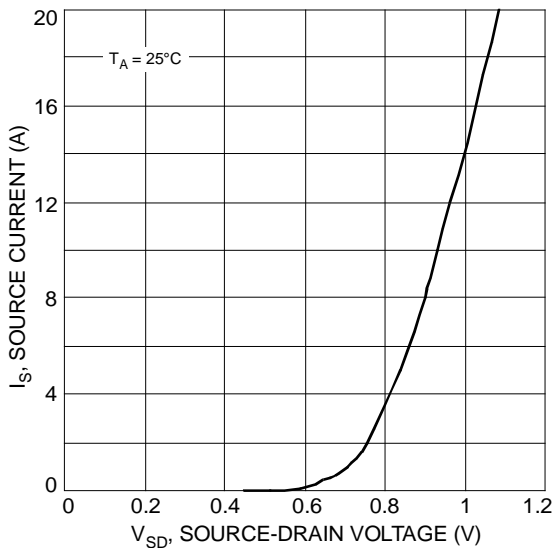


Fig. 7 Diode Forward Voltage vs. Current

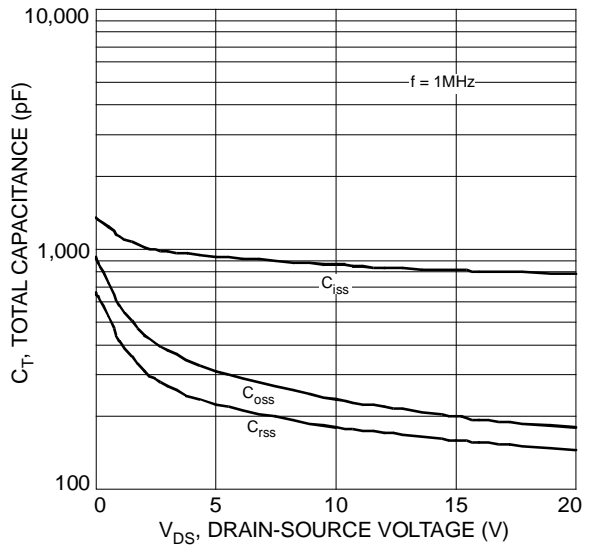
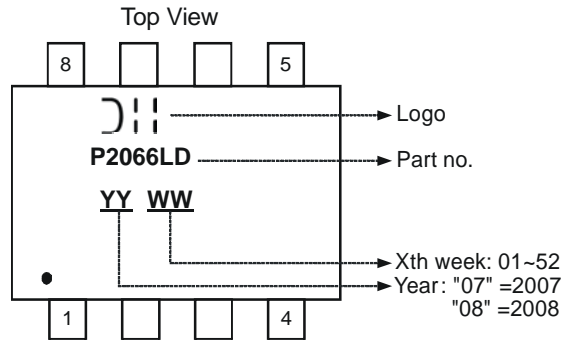
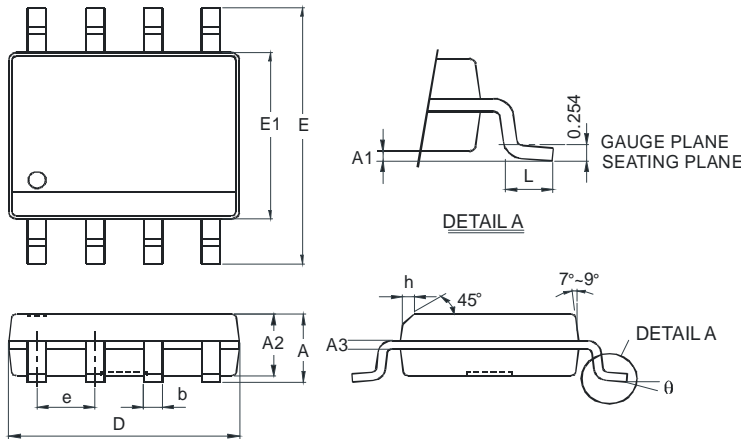


Fig. 8 Typical Total Capacitance

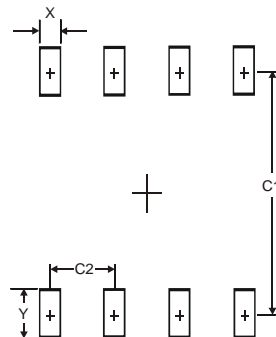
Ordering Information (Note 6)

Part Number	Case	Packaging
DMP2066LSD-13	SOP-8L	2500/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

Package Outline Dimensions


SOP-8L		
Dim	Min	Max
A	-	1.75
A1	0.08	0.25
A2	1.30	1.50
A3	0.20 Typ.	
b	0.3	0.5
D	4.80	5.30
E	5.79	6.20
E1	3.70	4.10
e	1.27 Typ.	
h	-	0.35
L	0.38	1.27
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout


Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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